ALPHA & OMEGA SEMICONDUCTOR

AOWF380A60C

600V αMOS5™ N-Channel Power Transistor

General Description

- Proprietary αMOS5™ technology
- Low $R_{DS(ON)}$
- Optimized switching parameters for better EMI performance
- Enhanced body diode for robustness and fast reverse recovery

Applications

- SMPS with PFC, Flyback and LLC topologies
- Silver ATX ,adapter, TV, lighting, Server power

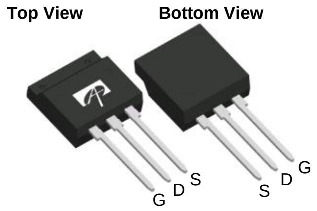
Product Summary

V_{DS} @ $T_{j,max}$	700V
I_{DM}	44A
$R_{DS(ON),max}$	< 0.38Ω
$Q_{g,typ}$	18nC
E_{oss} @ 400V	2.6µJ

100% UIS Tested
100% R_g Tested

Green Product

TO-262F



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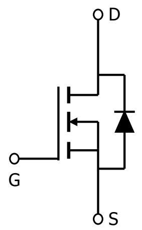


Orderable Part Number	Package Type	Form	Minimum Order Quantity
AOWF380A60C	TO262F	Tube	1000

Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	600	V
Gate-Source Voltage		V_{GS}	±20	V
Gate-Source Voltage (dynamic) AC(f>1Hz)		V_{GS}	±30	V
Continuous Drain Current	T_C=25°C	I_D	11*	A
	T_C=100°C		7.2*	
Pulsed Drain Current [C]		I_{DM}	44	
Avalanche Current [C]		I_{AR}	2.5	A
Repetitive avalanche energy [C]		E_{AR}	3.1	mJ
Single pulsed avalanche energy [G] (T_J=25°C, V_{GS}=10V, I_L=2Apk, L=105mH, R_{GS}=25Ω)		E_{AS}	210	mJ
MOSFET dv/dt ruggedness		dv/dt	100	V/ns
Peak diode recovery dv/dt			20	
Power Dissipation [B]	T_C=25°C	P_D	25	W
	Derate above 25°C		0.2	W/°C
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C
Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds		T_L	300	°C

Thermal Characteristics

Parameter	Symbol	Maximum	Units
Maximum Junction-to-Ambient [A,D]	$R_{\theta JA}$	65	°C/W
Maximum Junction-to-Case	$R_{\theta JC}$	5.0	°C/W

* Drain current limited by maximum junction temperature.

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V, T_J=25°C	600			V
		I_D=250µA, V_{GS}=0V, T_J=150°C		700		
BV_{DSS} /ΔTJ	Breakdown Voltage Temperature Coefficient	I_D=250µA, V_{GS}=0V		0.44		V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=600V, V_{GS}=0V			1	µA
		V_{DS}=480V, T_J=125°C			10	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±20V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=5V, I_D=250µA	2.6	3.2	3.8	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=5.5A		0.33	0.38	Ω
g_{FS}	Forward Transconductance	V_{DS}=10V, I_D=5.5A		9.3		S
V_{SD}	Diode Forward Voltage	I_S=5.5A, V_{GS}=0V		0.85	1.2	V
I_S	Maximum Body-Diode Continuous Current				11	A
I_{SM}	Maximum Body-Diode Pulsed Current [C]				44	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=100V, f=1MHz		955		pF
C_{oss}	Output Capacitance			29		pF
$C_{o(er)}$	Effective output capacitance, energy related [H]	V_{GS}=0V, V_{DS}=0 to 480V, f=1MHz		30		pF
$C_{o(tr)}$	Effective output capacitance, time related [I]			122		pF
C_{rss}	Reverse Transfer Capacitance	V_{GS}=0V, V_{DS}=100V, f=1MHz		2.4		pF
R_g	Gate resistance	f=1MHz		4.8		Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	V_{GS}=10V, V_{DS}=480V, I_D=5.5A		18		nC
Q_{gs}	Gate Source Charge			7		nC
Q_{gd}	Gate Drain Charge			4.5		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=400V, I_D=5.5A, R_G=5Ω		20		ns
t_r	Turn-On Rise Time			13		ns
$t_{D(off)}$	Turn-Off DelayTime			43		ns
t_f	Turn-Off Fall Time			16		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=5.5A, dI/dt=100A/µs, V_{DS}=400V		251		ns
I_{rm}	Peak Reverse Recovery Current			19		A
Q_{rr}	Body Diode Reverse Recovery Charge			3.1		µC

A. The value of $R_{\theta JA}$ is measured with the device in a still air environment with T_A =25° C.
B. The power dissipation P_D is based on $T_{J(MAX)}$=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150° C, Ratings are based on low frequency and duty cycles to keep initial T_J =25° C.
D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.
E. The static characteristics in Figures 1 to 6 are obtained using <300µs pulses, duty cycle 0.5% max.
F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=150° C. The SOA curve provides a single pulse rating.
G. This is the absolute maximum rating. Parts are 100% tested at T_J=25° C, L=60mH, I_{AS}=1A, V_{DD}=150V, R_G=25Ω.
H. $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% $V_{(BR)DSS}$.
I. $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% $V_{(BR)DSS}$.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

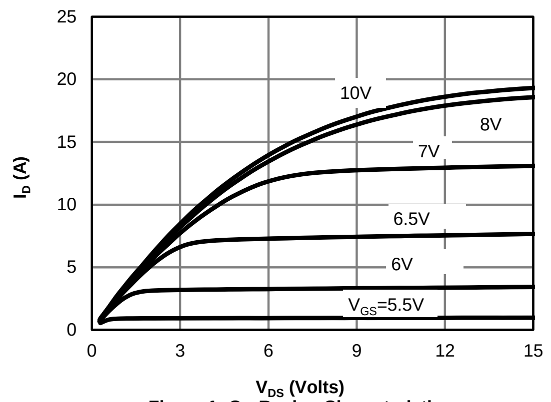


Figure 1: On-Region Characteristics

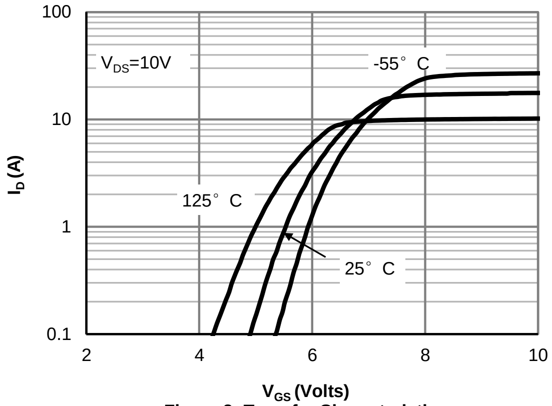


Figure 2: Transfer Characteristics

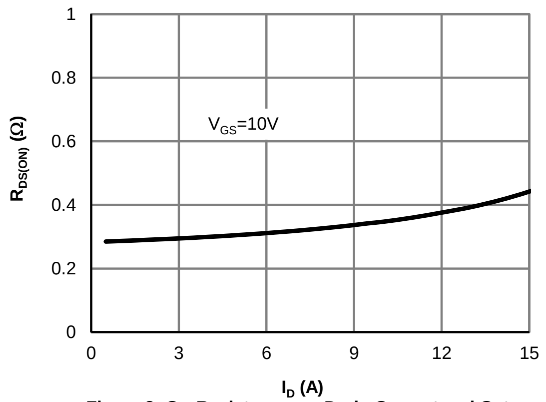


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

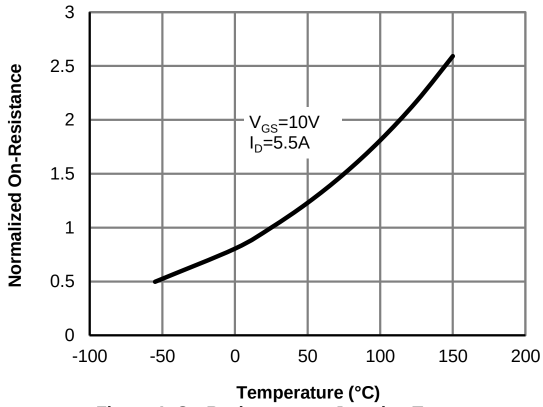


Figure 4: On-Resistance vs. Junction Temperature

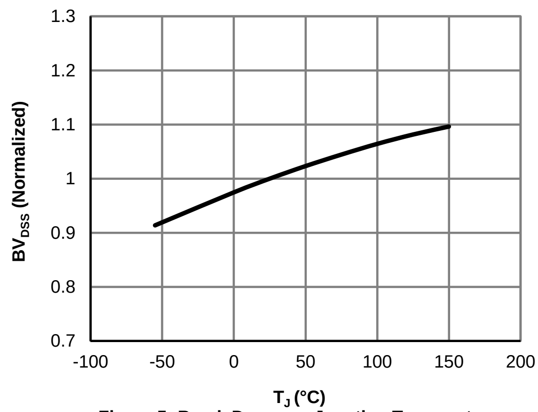


Figure 5: Break Down vs. Junction Temparature

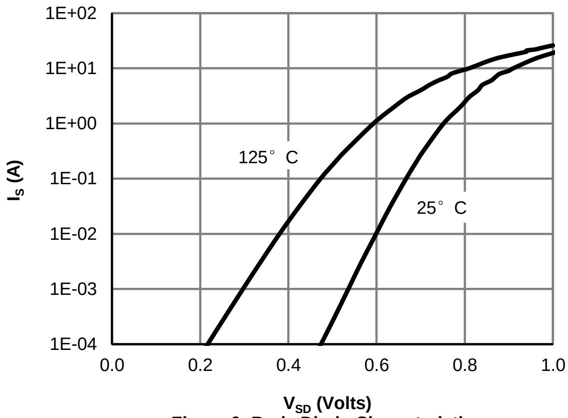


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

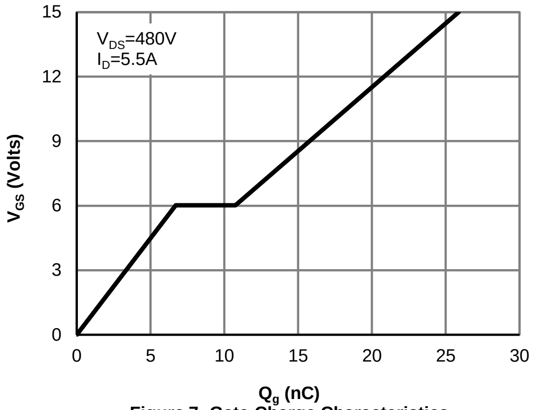


Figure 7: Gate-Charge Characteristics

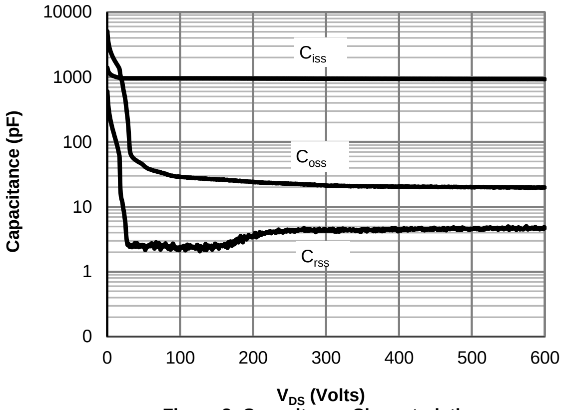


Figure 8: Capacitance Characteristics

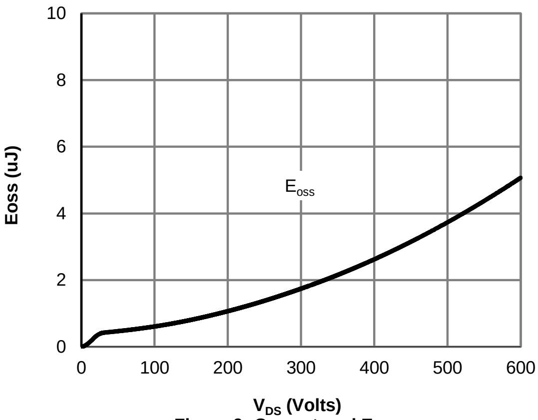


Figure 9: Coss stored Energy

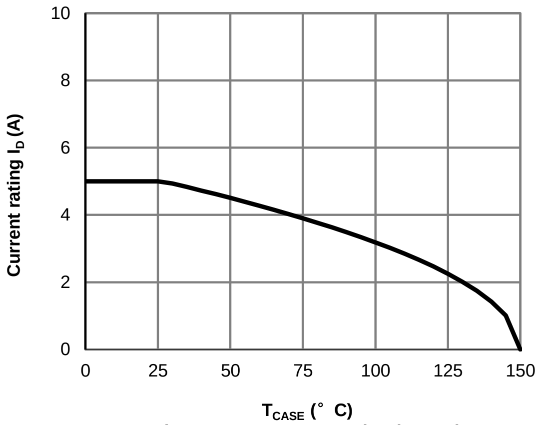


Figure 10: Current De-rating (Note F)

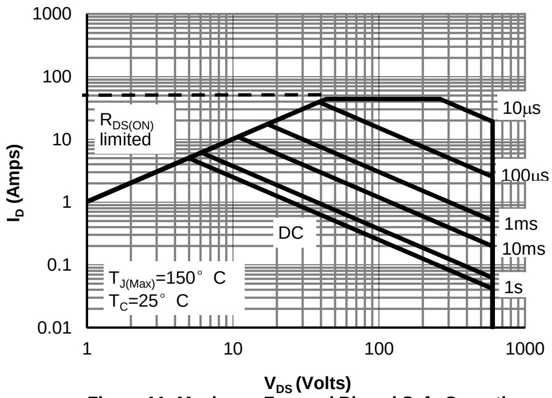


Figure 11: Maximum Forward Biased Safe Operating Area (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

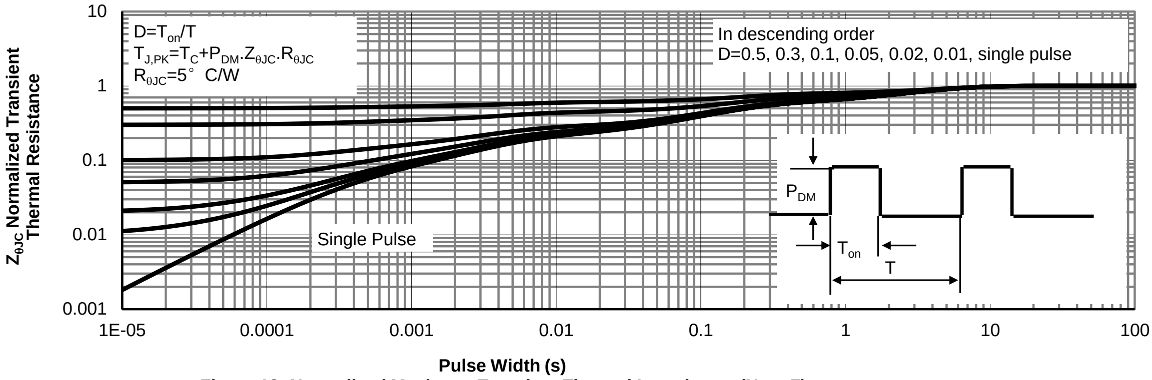
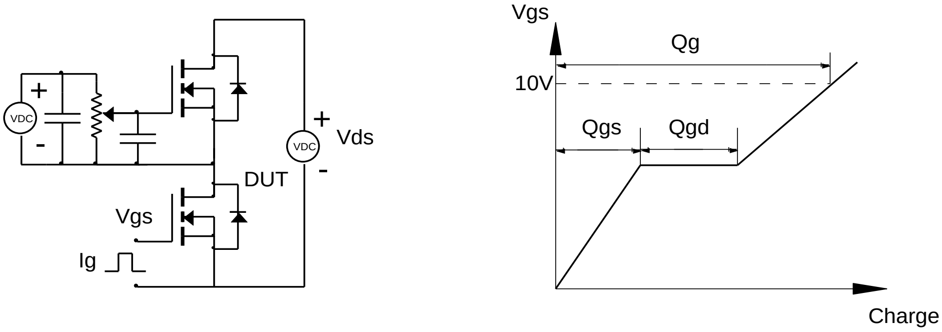
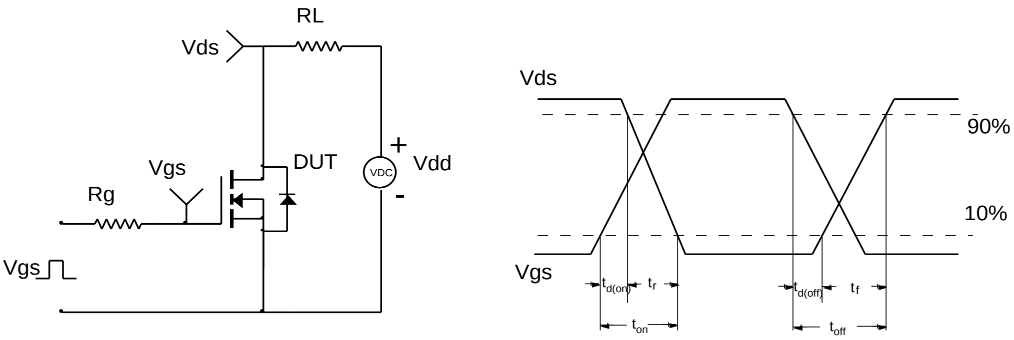


Figure 12: Normalized Maximum Transient Thermal Impedance (Note F)

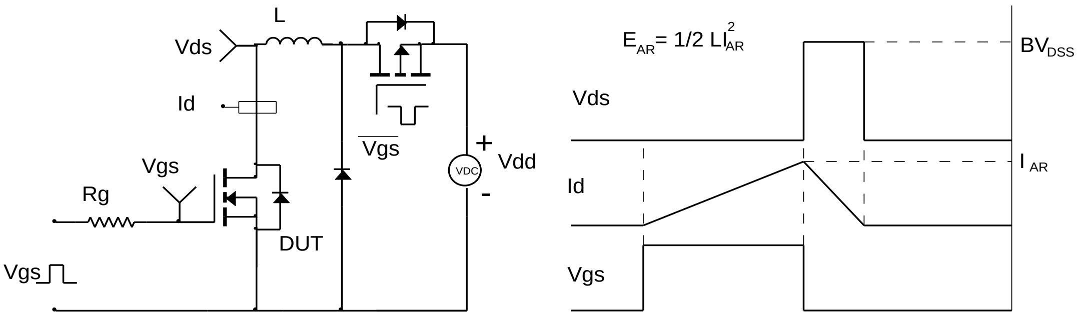
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms